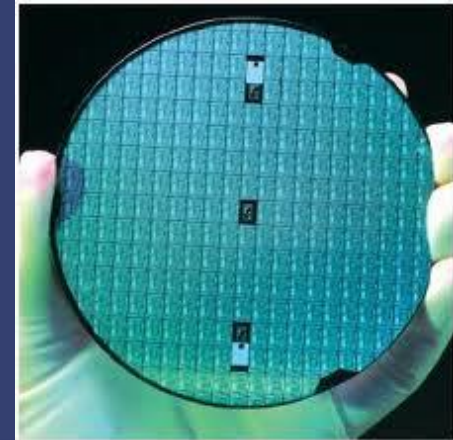
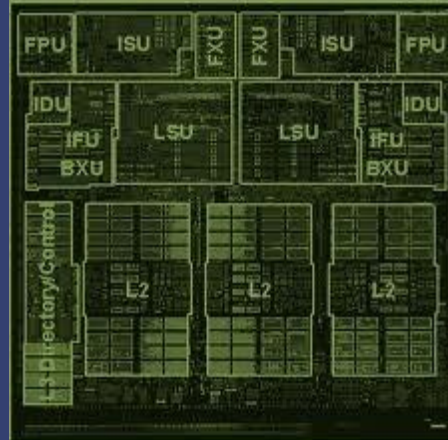
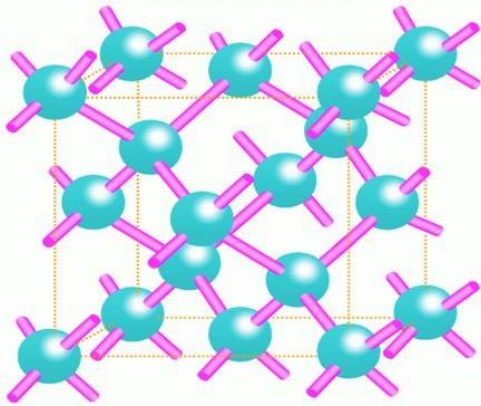


Structure of silicon crystal



ECE 225

Lecture 13

Nanoscale Power and Thermal Management: Self-consistent Thermal Profile Estimation Design-Specific Metric Optimization IC Cooling Analysis

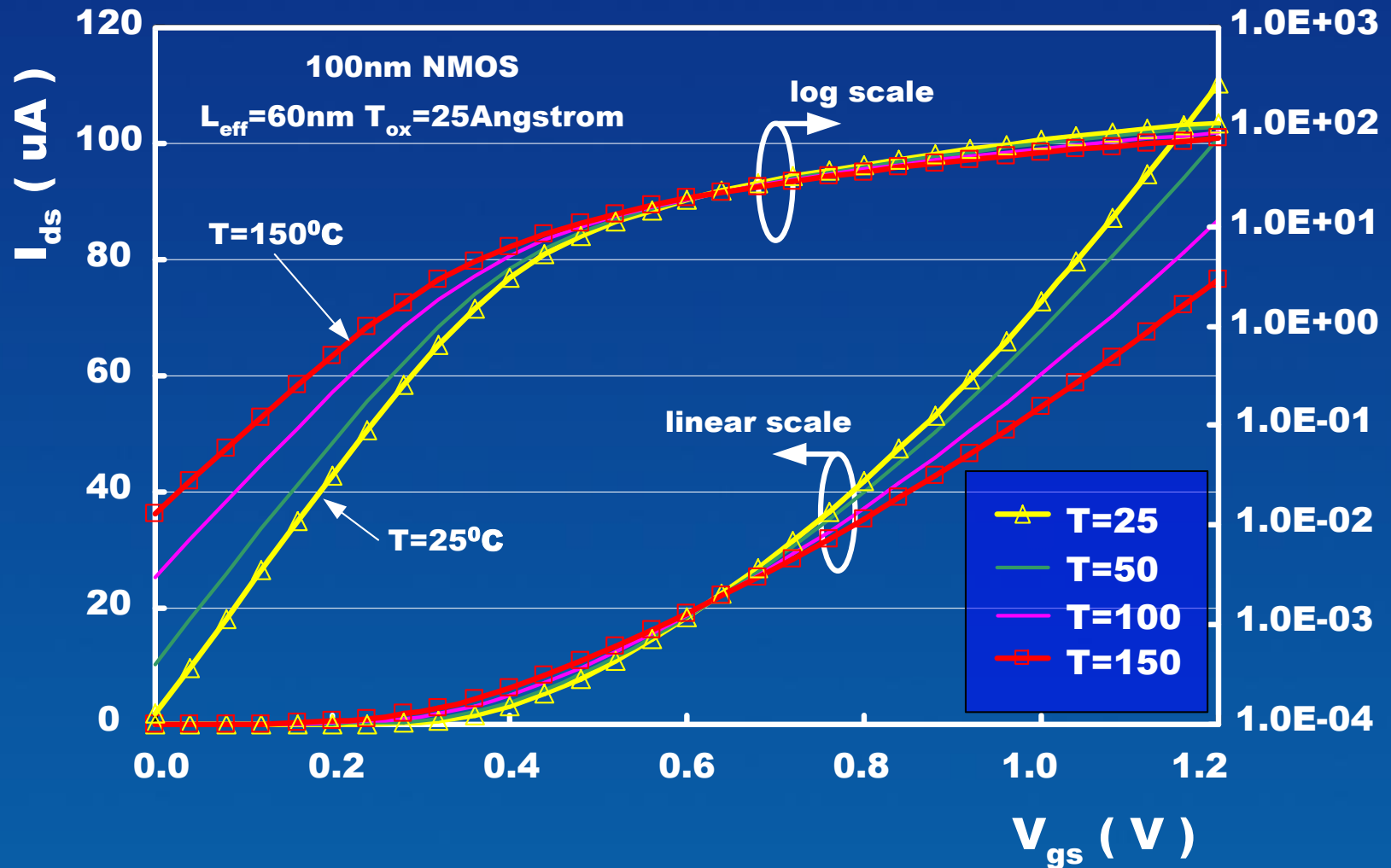
*Prof. Kaustav Banerjee
Electrical and Computer Engineering
University of California, Santa Barbara*

Self-Consistent Temperature Profile Estimation

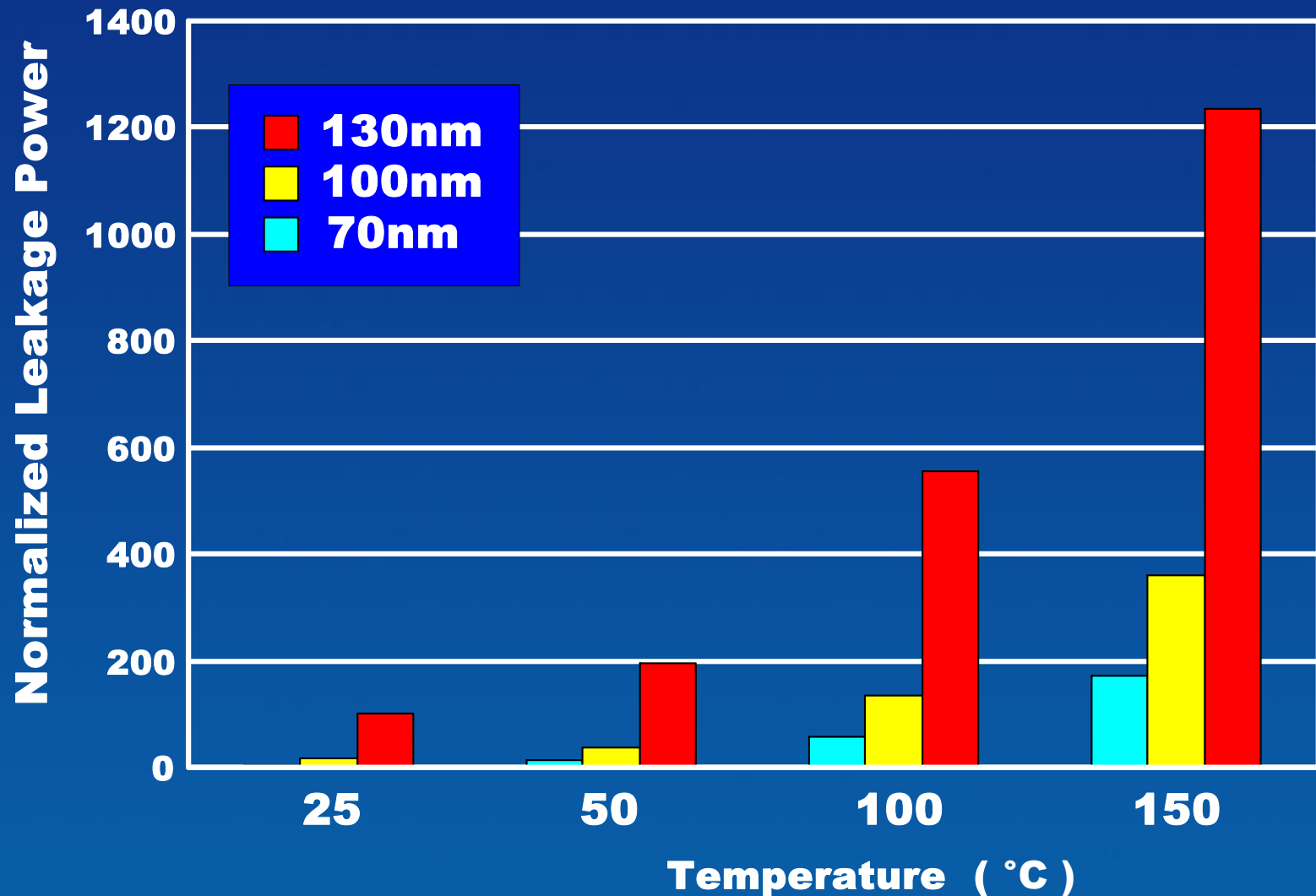
S-C. Lin, G. Chrysler, R. Mahajan, V. De and K. Banerjee, “A Self-Consistent Substrate Thermal Profile Estimation Technique for Nanoscale ICs—Part I: Electrothermal Couplings and Full-Chip Package Thermal Model,” TED Vol. 54, No. 12, pp. 3342-3350, 2007.

S-C. Lin, G. Chrysler, R. Mahajan, V. De and K. Banerjee, “A Self-Consistent Substrate Thermal Profile Estimation Technique for Nanoscale Part II: Implementation and Implications for Power Estimation and Thermal Management,” TED Vol. 54, No. 12, pp. 3351-3360, 2007.

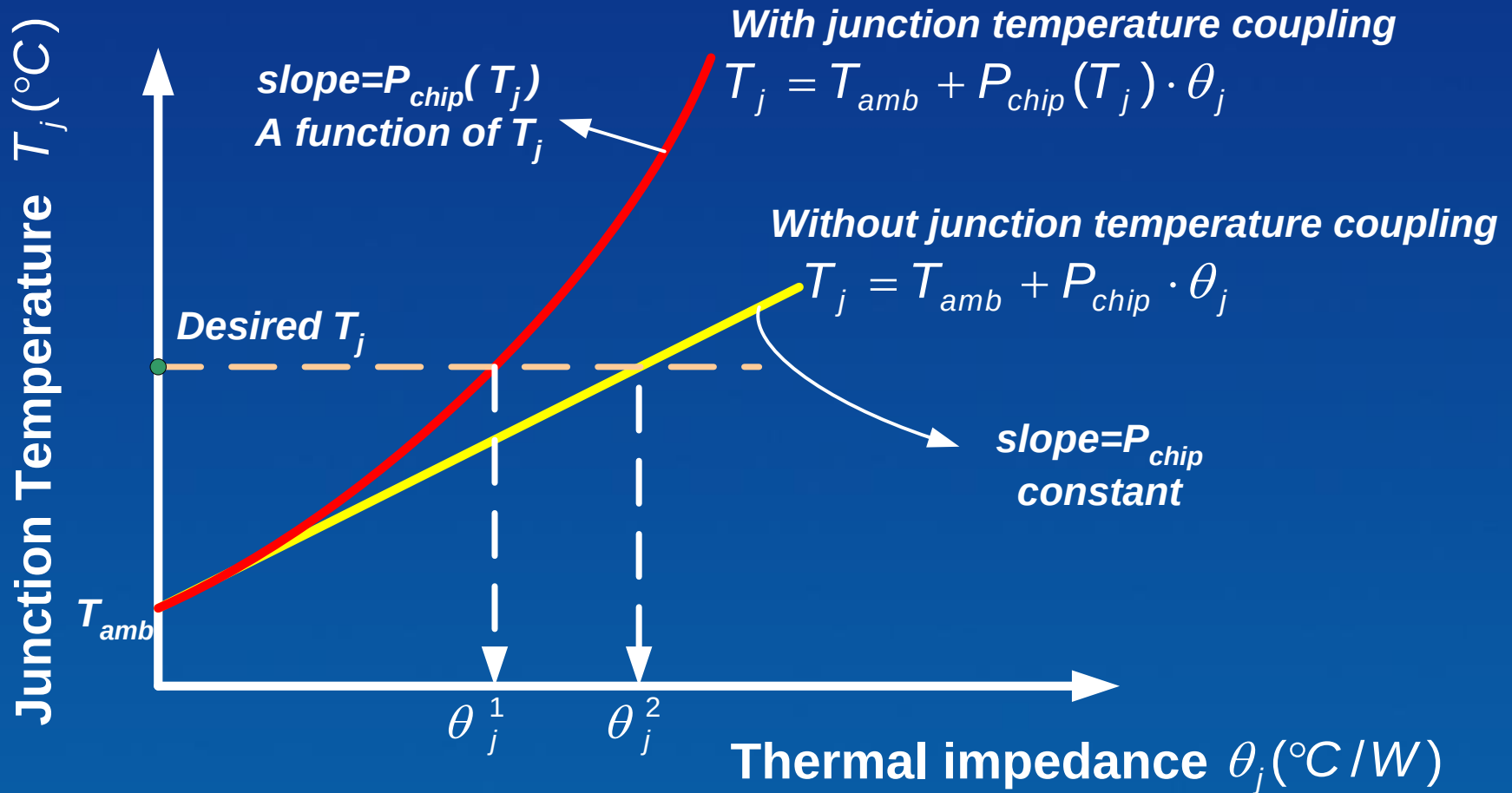
Subthreshold Leakage Current



Leakage Power Scaling



P_{chip} dependency



Coupling Models

$$F = f_1(V_{dd}, V_t, T_j, L_{nom}, \Delta V_t)$$

$$P_{wa} = \alpha C V_{dd}^2 F$$

$$P_{wsl} = f_2(V_{dd}, V_t, T_j, L_{nom}, \Delta V_t)$$

$$P_{wgl} = f_3(V_{dd}, V_t, t_{ox})$$

$$R = f_4(V_{dd}, V_t, T_j, L_{nom}, \Delta V_t, t_{ox})$$

$$\Delta V_t = f_5(L_{nom}, t_{ox}, X_j, V_{dd}, \Delta L)$$

$$T_j = T_{amb} + \theta_j (P_{wa} + P_{wsl} + P_{wgl})$$

$F \rightarrow$ Frequency

$P_{wa} \rightarrow$ Active Power

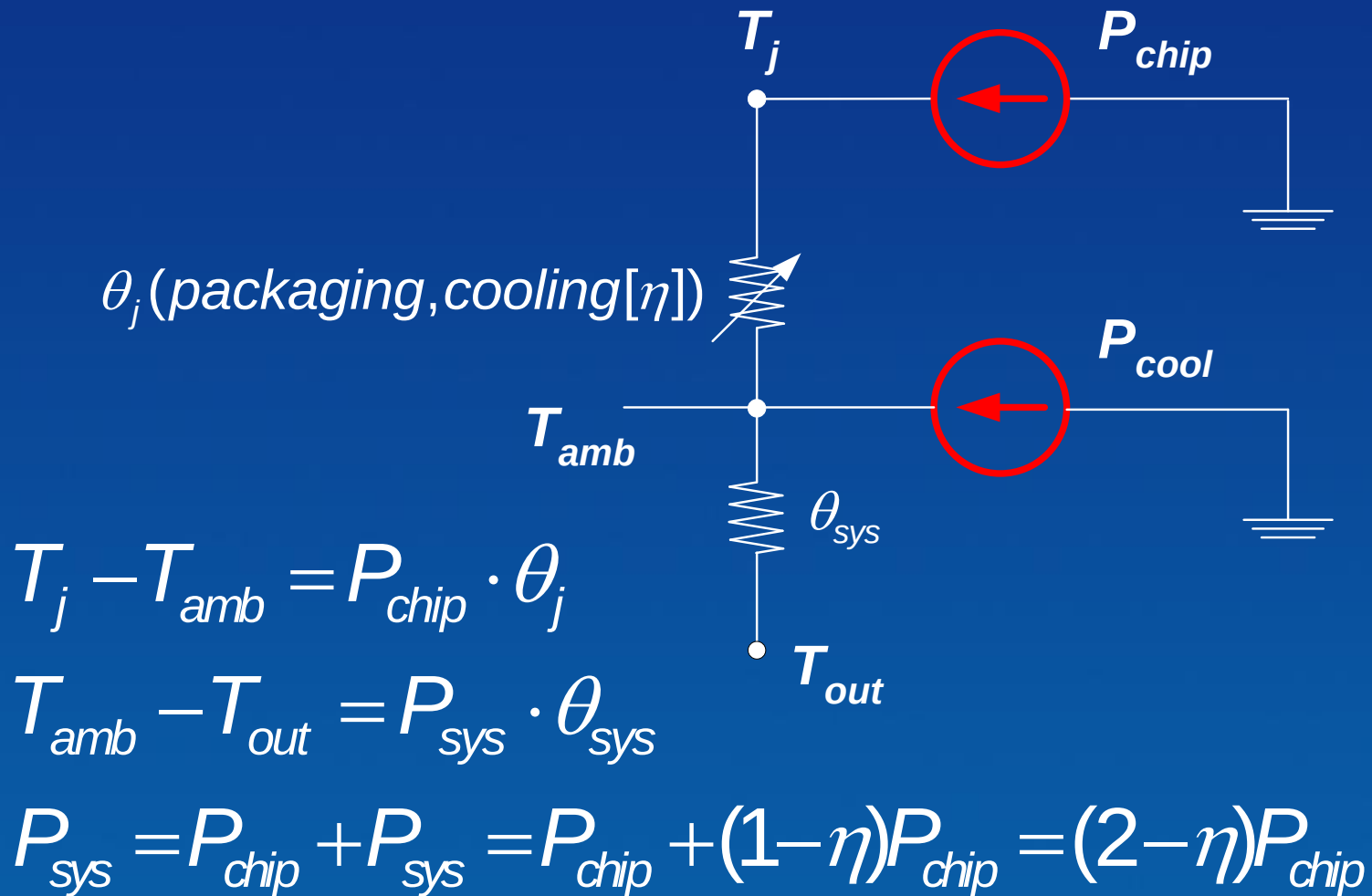
$P_{wsl} \rightarrow$ Subthreshold Leakage

$P_{wgl} \rightarrow$ Gate Leakage

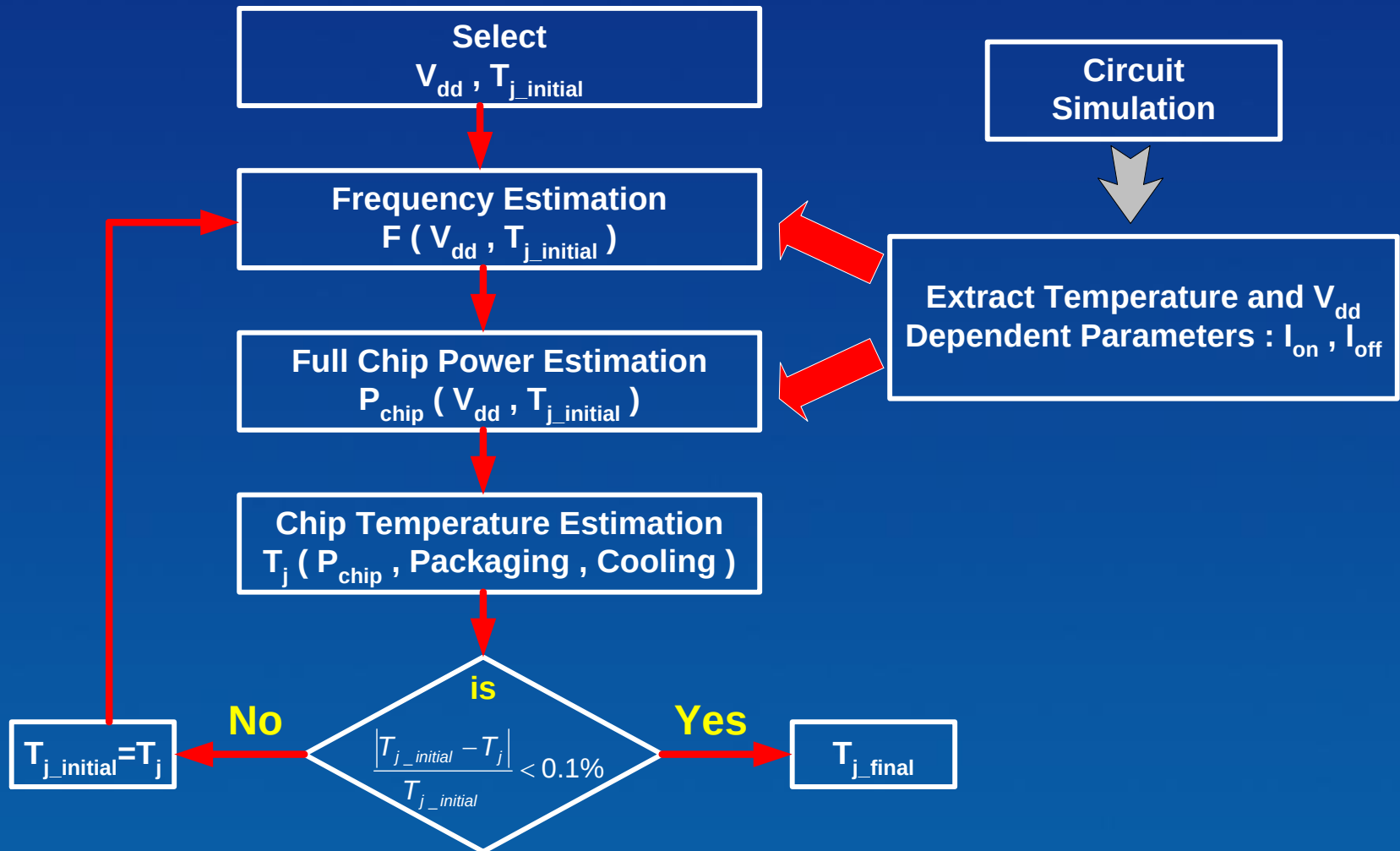
$R \rightarrow$ Reliability Factor

$\Delta V_t \rightarrow$ Threshold Voltage Variation

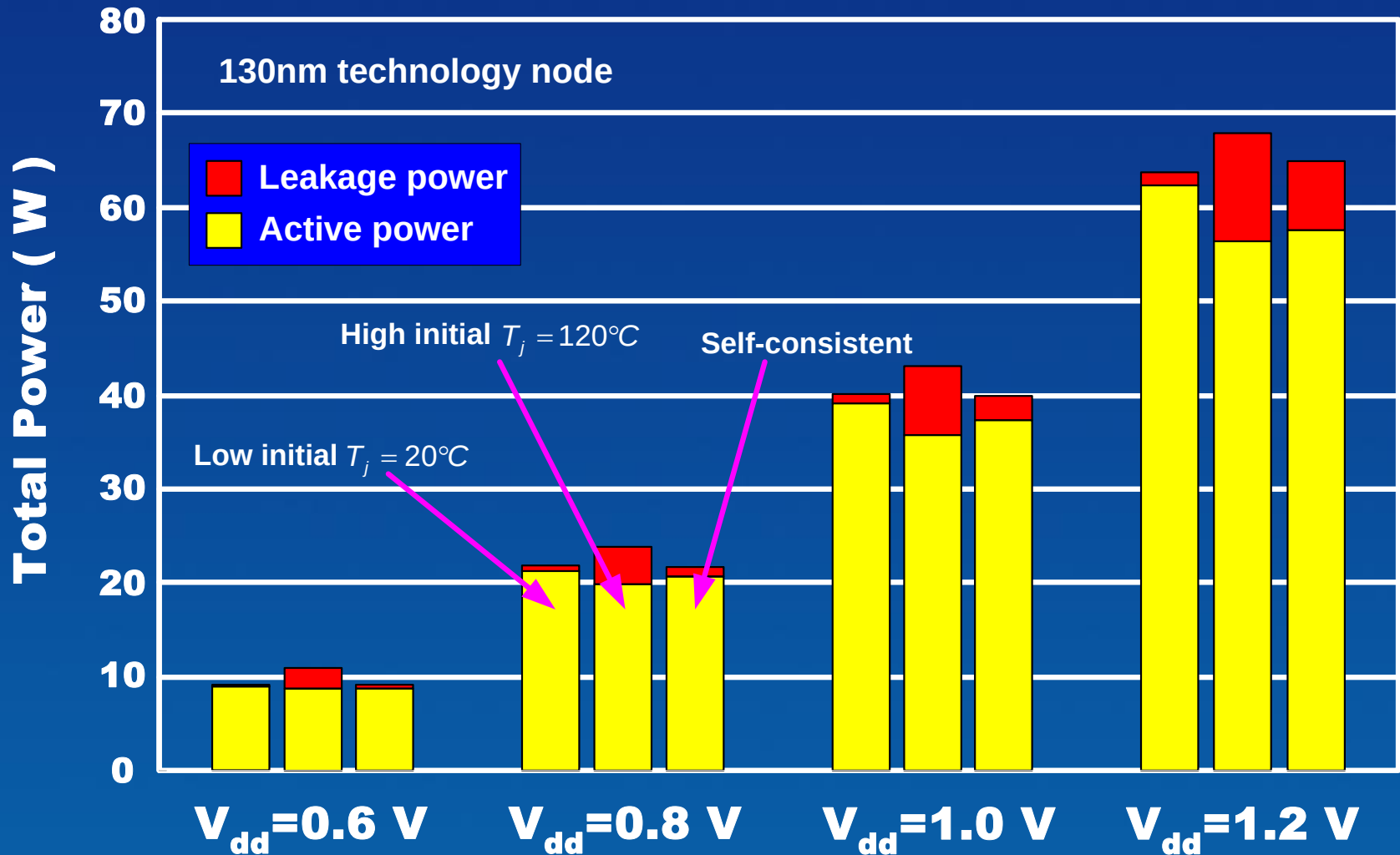
Equivalent Thermal Circuit



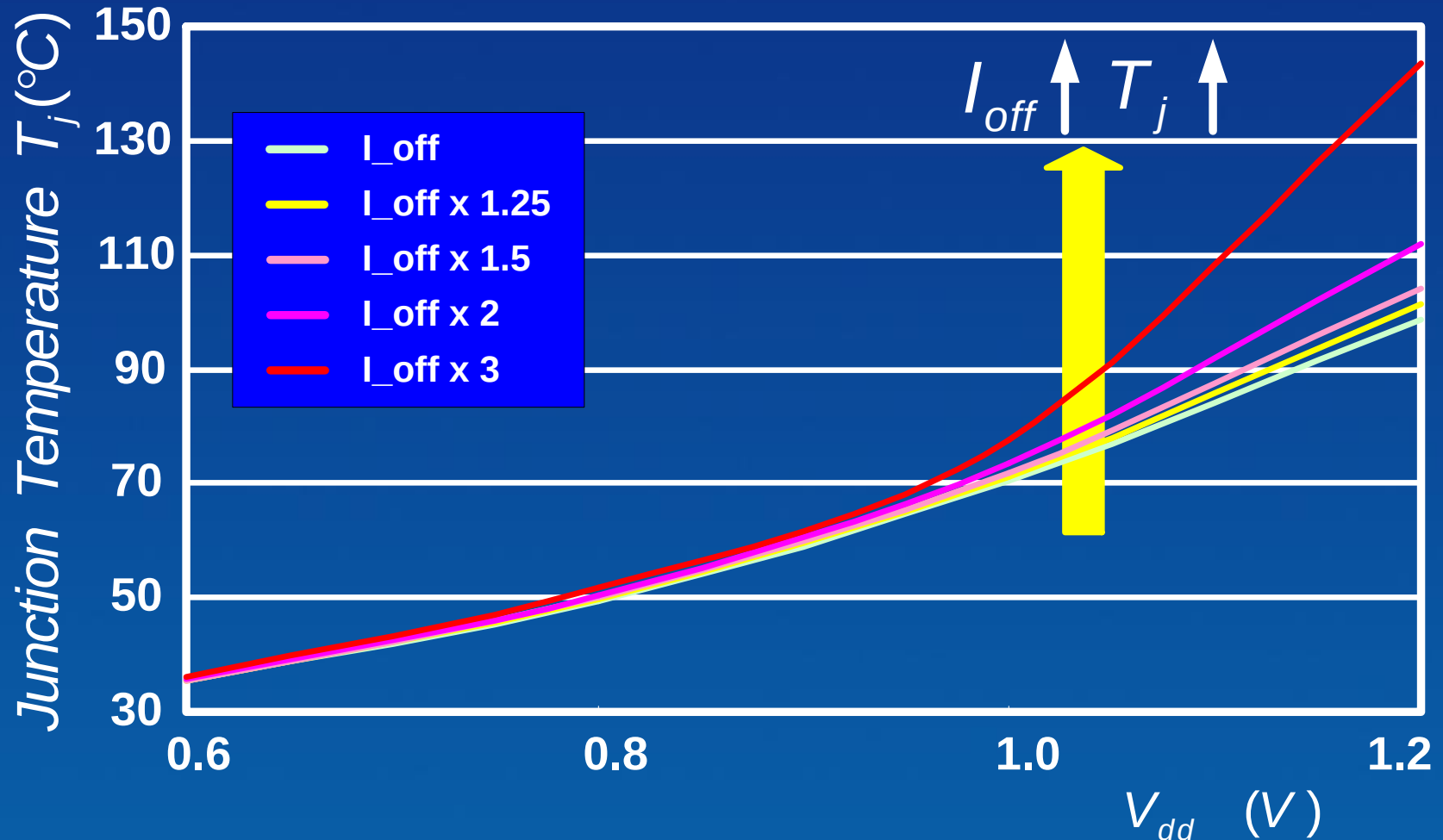
Overview



Total Power Dissipation

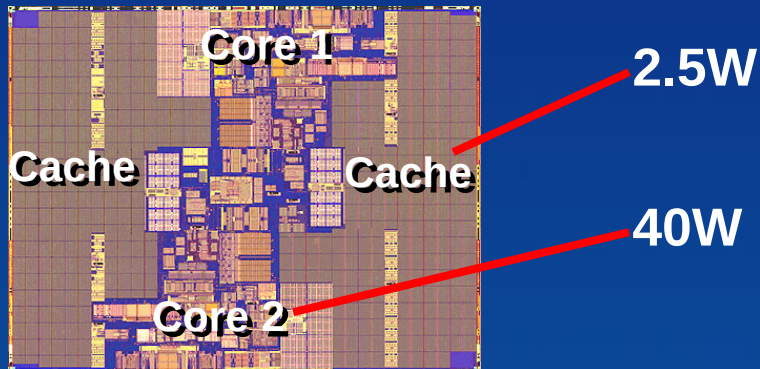


Self-Consistent Junction Temperature

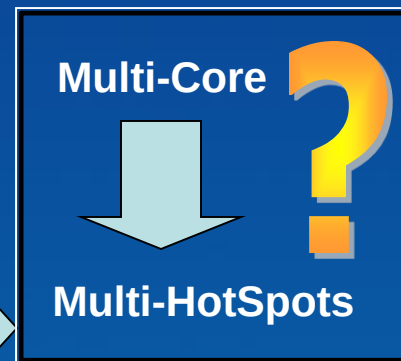
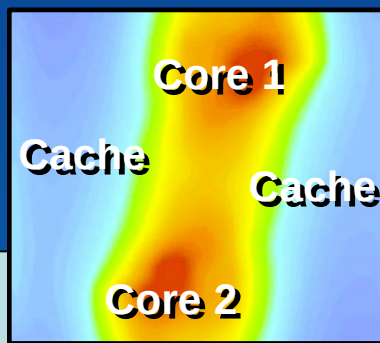
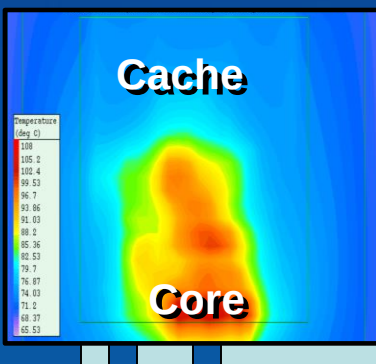
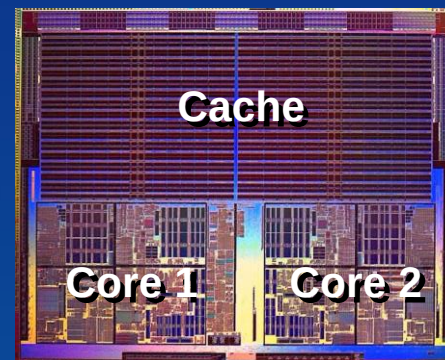


Non-Uniform Power Density

Intel's first dual-core
Itanium-Montecito 90nm



AMD's first dual-core
Athlon 64 X2 90nm SOI

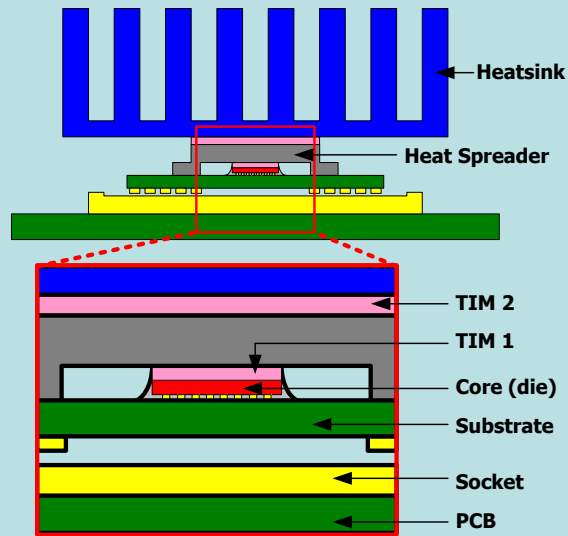


S. Borkar, DAC 2003 C. Poirier, ISSCC 2005

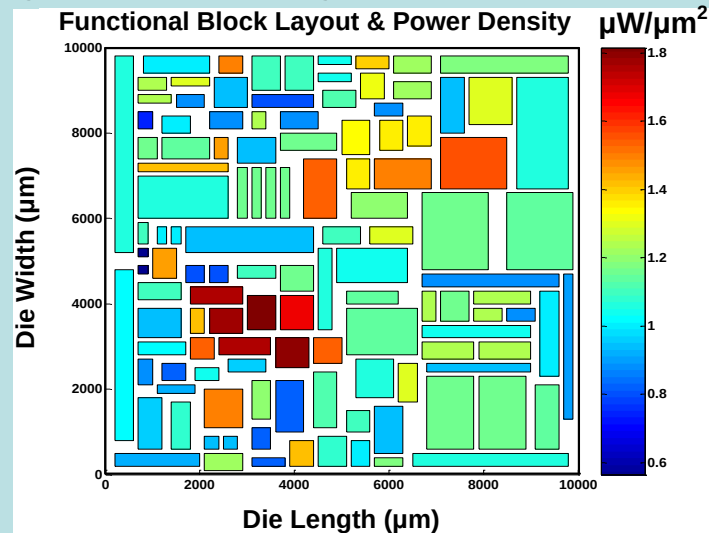
Non-uniform power density generates on-chip temperature gradient

Methodology Overview

Packaging / Cooling Model



Layout Geometry & Power Dissipation



$$\frac{\partial T}{\partial n_i} = \frac{h}{K} [T - T_{amb}]$$

Boundary Condition

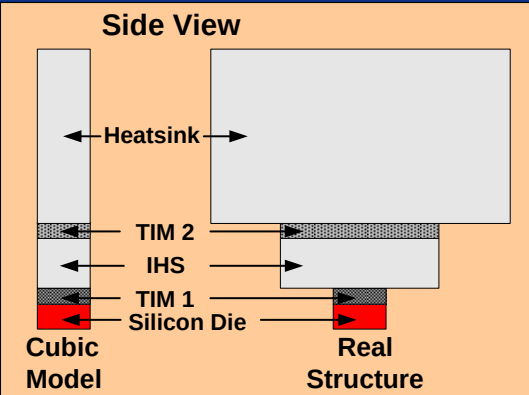
$$\frac{\partial T}{\partial t} = \left(\frac{K}{\rho C_p} \right) \left(\frac{\partial^2 T}{\partial x^2} + \frac{\partial^2 T}{\partial y^2} + \frac{\partial^2 T}{\partial z^2} \right) + \frac{p}{\rho C_p}$$

Parabolic Heat
Partial Differential Equations

Electrothermal
Couplings

3-D Electrothermally-Aware
Spatial Temperature Estimation

Numerical Approach



$$\frac{\partial T}{\partial t} = \frac{k}{\rho C_p} \left(\frac{\partial^2 T}{\partial x^2} + \frac{\partial^2 T}{\partial y^2} + \frac{\partial^2 T}{\partial z^2} \right) + \frac{p}{\rho C_p}$$

$$\beta_x = \frac{k \Delta t}{2 \Delta x^2 \rho C_p}$$

Crank-Nicholson
Implicit Method

$$\frac{M_x T}{\Delta x^2} = \frac{T_{i+1,j,k} - 2T_{i,j,k} + T_{i-1,j,k}}{\Delta x^2}$$

$$\frac{\partial^2 T}{\partial x^2} = \frac{1}{2} \left(\frac{M_x T^{n+1}}{\Delta x^2} + \frac{M_x T^n}{\Delta x^2} \right)$$

$$\frac{T^{n+1} - T^n}{\Delta t} = \left(\frac{k}{\rho C_p} \right) \left[\left(\frac{M_x}{2 \Delta x^2} + \frac{M_y}{2 \Delta y^2} + \frac{M_z}{2 \Delta z^2} \right) (T^{n+1} + T^n) \right] + \frac{p}{\rho C_p}$$

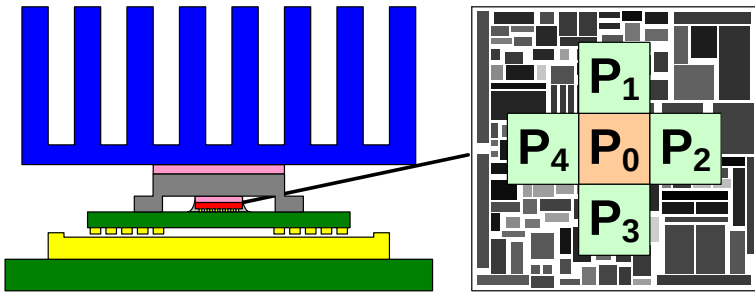
$$(1 - \beta_x M_x - \beta_y M_y - \beta_z M_z)(T^{n+1} - T^n) = 2(\beta_x M_x + \beta_y M_y + \beta_z M_z)T^n + \frac{\Delta t}{\rho C_p} p$$

$$(1 - \beta_x M_x)(1 - \beta_y M_y)(1 - \beta_z M_z)(T^{n+1} - T^n) = 2(\beta_x M_x + \beta_y M_y + \beta_z M_z)T^n + \frac{\Delta t}{\rho C_p} p$$

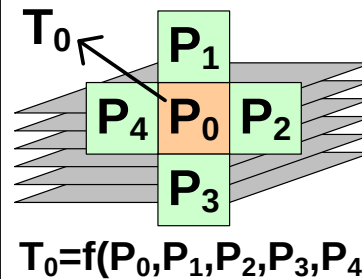
Linear Equations: $(1 - \beta_x M_x)U_{x,y,z} = V_{x,y,z}$

Self-Consistent Evaluation

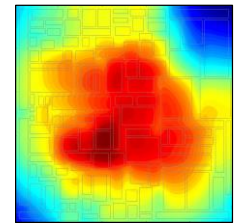
Package & Power Distribution



Traditional Evaluation

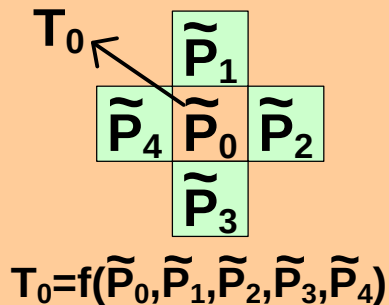


Steady-State Temperature Profile

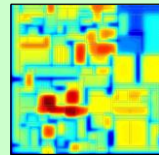


Update temperature dependent power

Self-Consistent Evaluation

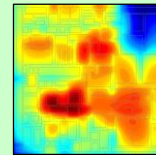


From $P(t_0)$
Solve $T(t_0 + \Delta t)$



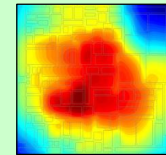
$P(t_0) \rightarrow P(t_0 + \Delta t)$

From $P(t_0 + \Delta t)$
Solve $T(t_0 + 2\Delta t)$



$P(t_0 + \Delta t) \rightarrow P(t_0 + 2\Delta t)$

Steady-State
Temperature profile



Steady-State P

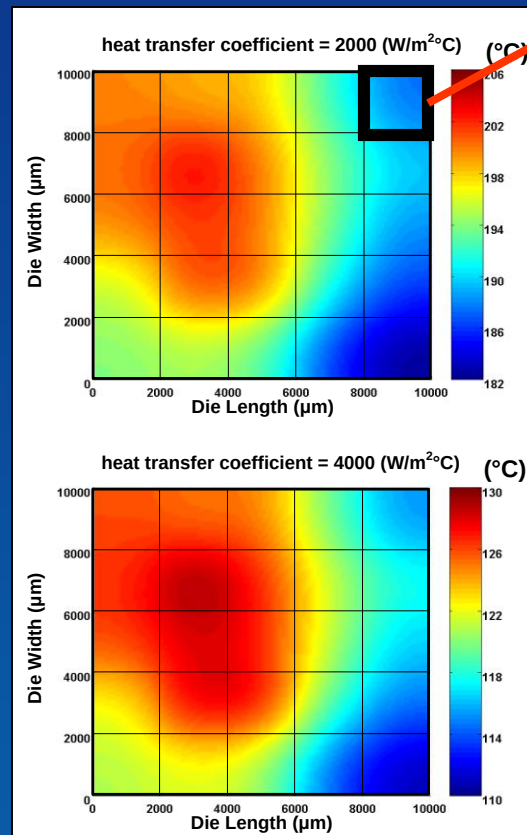
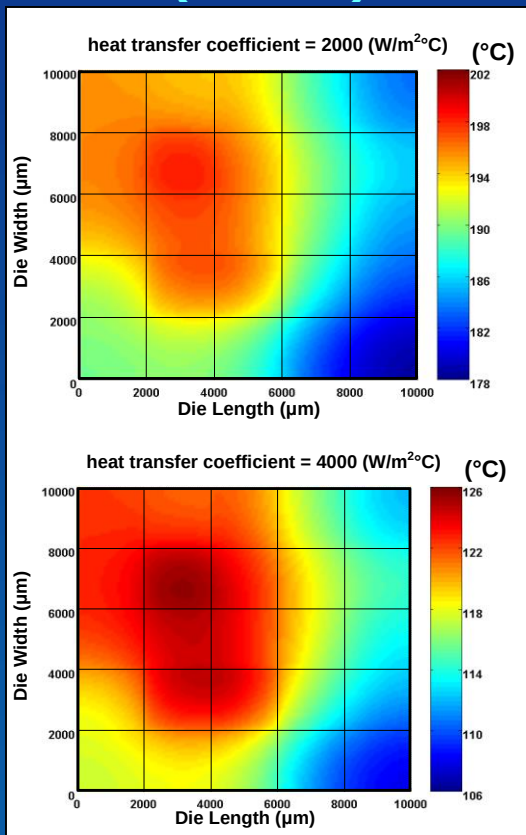
Methodology Verification

For a case with negligible leakage

Commercial Tool
(IcePak)

Proposed Method

Equally select 400 data points
from identical locations for
comparison (total = 10000 pts)

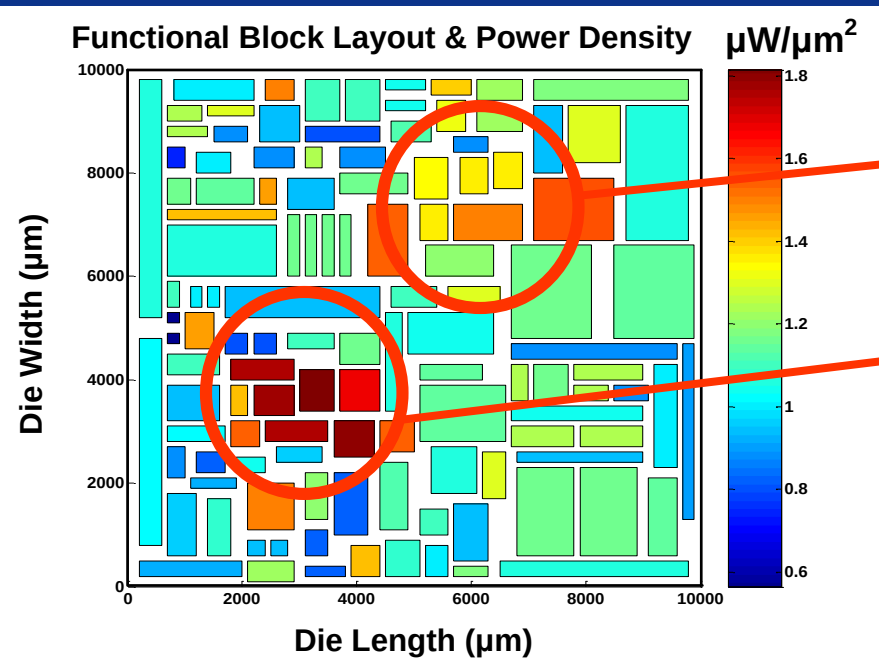


Coefficient	Max. Deviation
h=1000	2.13 %
h=2000	2.48%
h=3000	3.26 %
h=4000	3.28 %
h=5000	3.06 %

Proposed method is validated against an industrial-quality software.



Implementation & Setup



High leakage power region

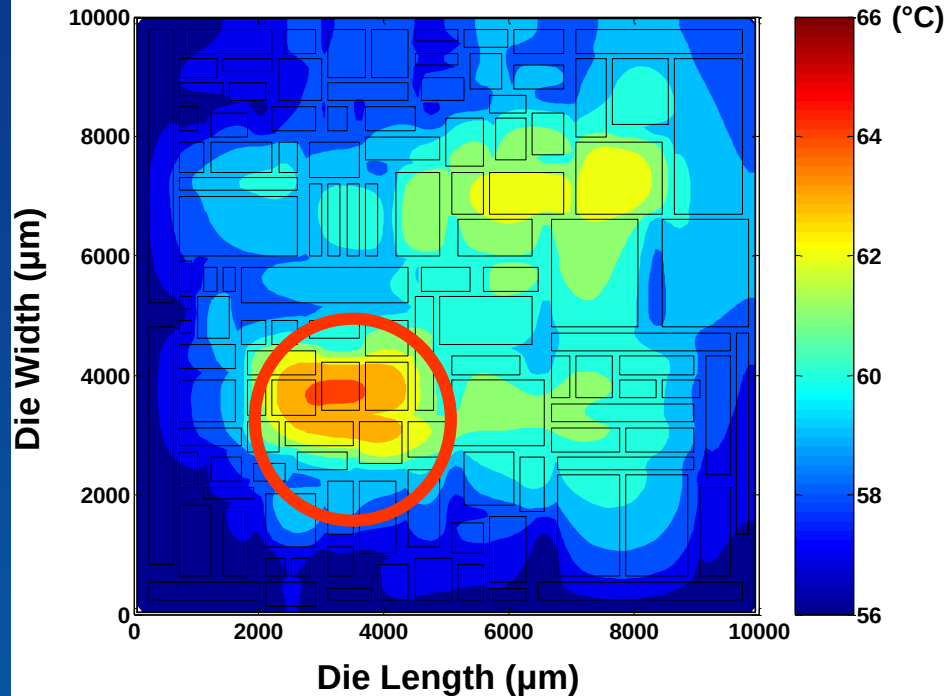
High power density region

Layer	Area (mm^2)	Thickness (mm)	Specific Heat ($\text{J}/\text{kg}^\circ\text{C}$)	Density (kg/m^3)	K ($\text{W}/\text{m}^\circ\text{C}$)
Die	10 X 10	0.8	712	2330	120
TIM 1	10 X 10	0.2	230	7310	30
IHS	30 X 30	1.8	385	8930	390
TIM 2	30 X 30	0.2	2890	900	6.4
Heatsink	60 X 60	6.4	385	8930	360

Impact of Considering ET-couplings

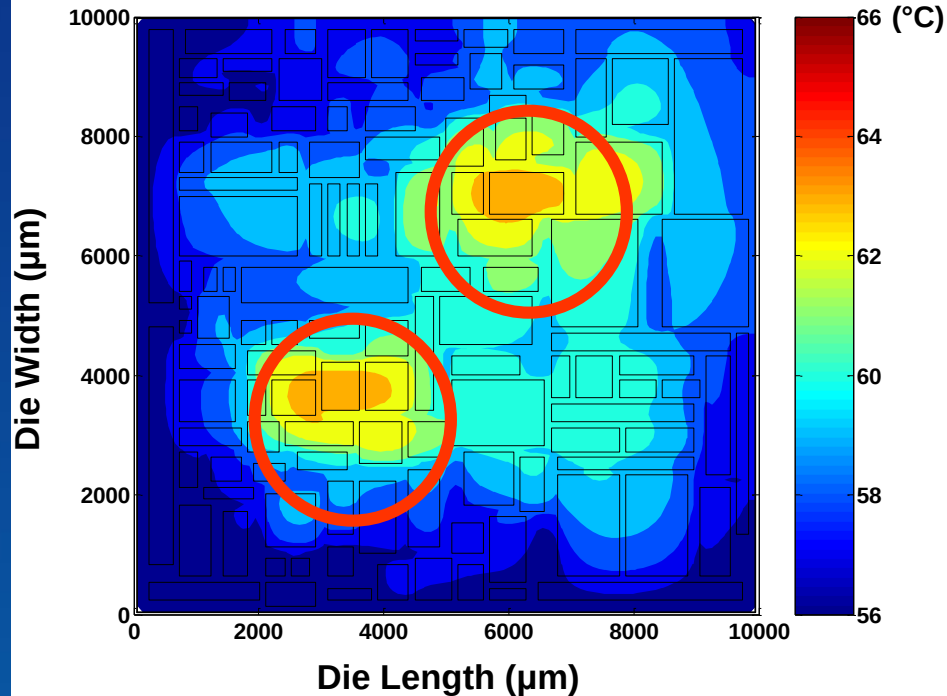
Without ET-Couplings

Traditional Evaluation + Realistic Package Thermal Model



With ET-Couplings

Electrothermally-Aware + Realistic Package Thermal Model

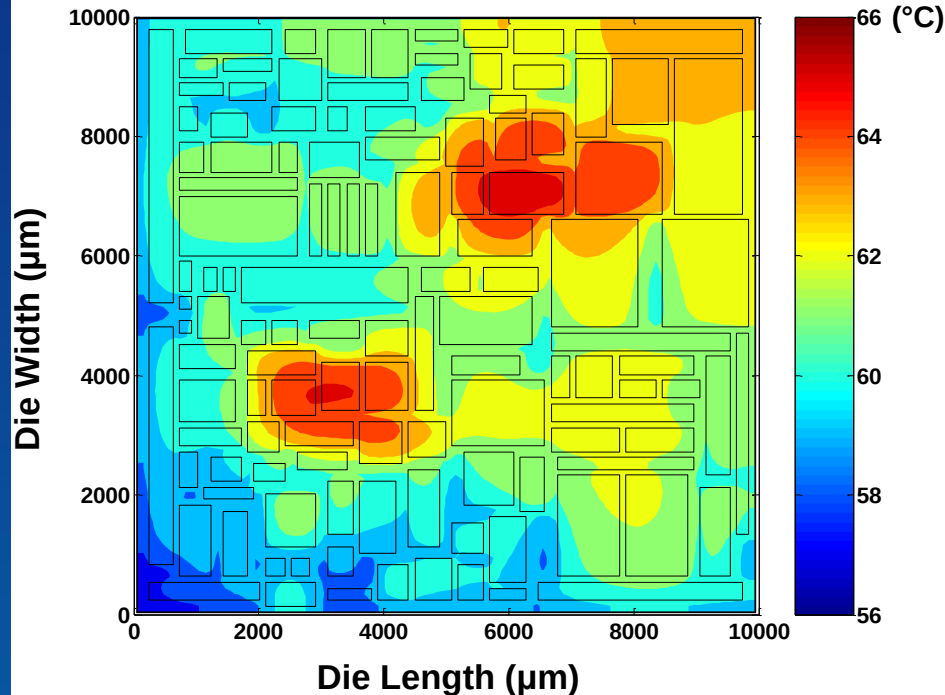


- ❖ Traditional evaluation neglects electrothermal couplings
- ❖ Considering electrothermal couplings leads to an additional hot-spot at the highest leakage power region

Impact of Package Models

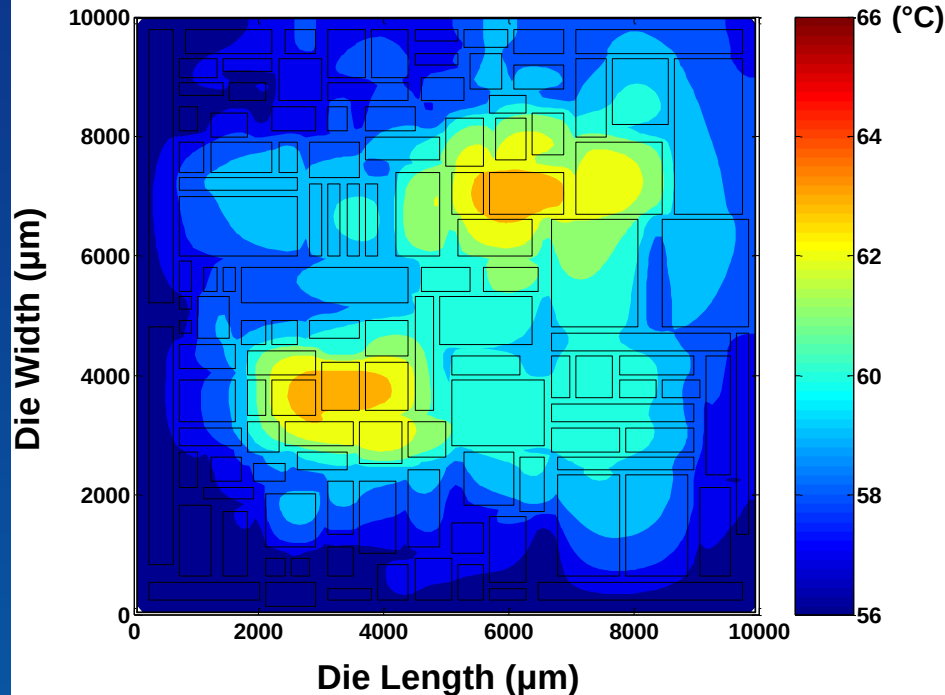
Cubic Package Thermal Model

Electrothermally-Aware + Cubic Package thermal Model



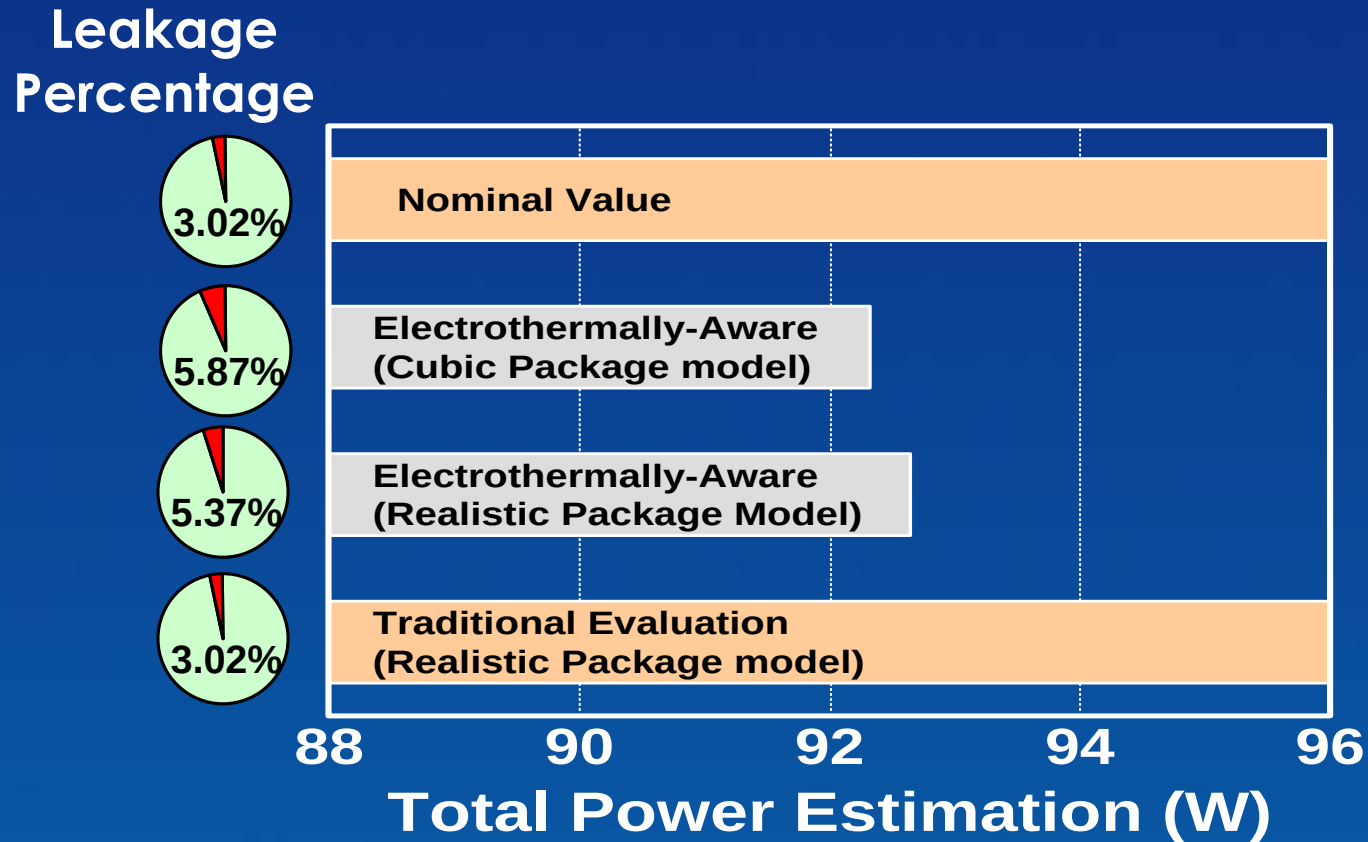
Realistic Package Thermal Model

Electrothermally-Aware + Realistic Package Thermal Model



- ❖ Simple cubic package thermal model ignores physical dimensions of different packaging layers and neglects lateral heat spreading
- ❖ Simple cubic model over-estimates the temperature profile

Implications for Power Estimation



- ❖ Power is not consistent with temperature in traditional evaluation
- ❖ Considering cubic package model overestimates leakage power

Design-Specific Metric Optimization

S-C. Lin and K. Banerjee, "A Design-Specific and Thermally-Aware Methodology for Trading-Off Power and Performance in Leakage-Dominant CMOS Technologies," TVLSI Vol. 16, No. 11, pp. 1488-1498, 2008.

Target:

Find a minimal value of Energy-Delay-Product for operation.

M. Horowitz, 1997

Delay

Delay of various gates in the critical path remains proportional to the delay of an equivalent inverter.

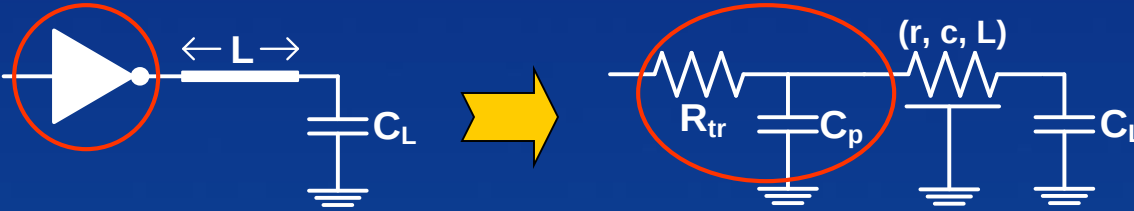
Can be evaluated by Alpha-Power model

T. Sakurai and A. R. Newton, 1990

Energy

Can be calculated by total power dissipation

Incorporate Interconnect Effects in EDP Optimization



$$\tau = R_{tr}(C_p + C_L + cL) + rLC_L + \left(\frac{1}{2}\right)rcL^2$$

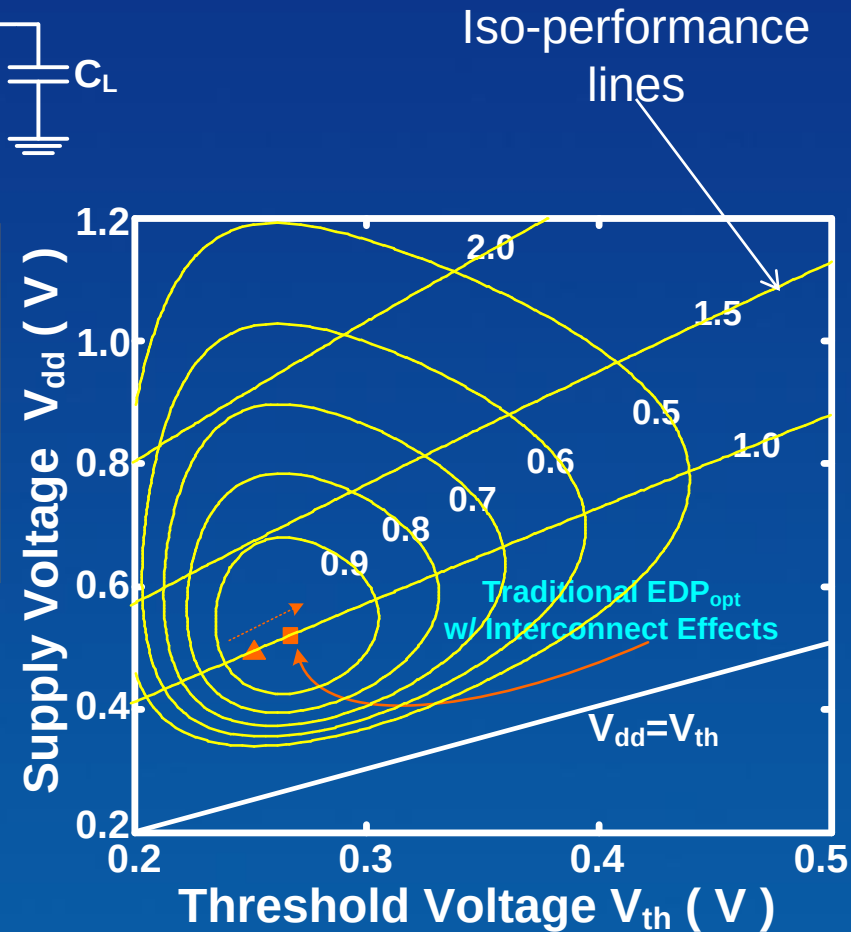
$$T_g \cong 0.69R_{tr}(C_p + C_L + cL) + 0.69rLC_L + 0.38rcL^2$$

$$T_g \cong \frac{KV_{dd}}{(V_{dd} - V_{th})^\alpha} \left[1 + \frac{cL}{C_p + C_L} \right] + 0.69rLC_L + 0.38rcL^2$$

$$P_{dynamic} = aC_{eff}V_{dd}^2F$$

$$P_{static} = I_s e^{-V_{th}/\gamma V_o} (1 - e^{-V_{ds}/\gamma V_o}) W_{eff} V_{dd}$$

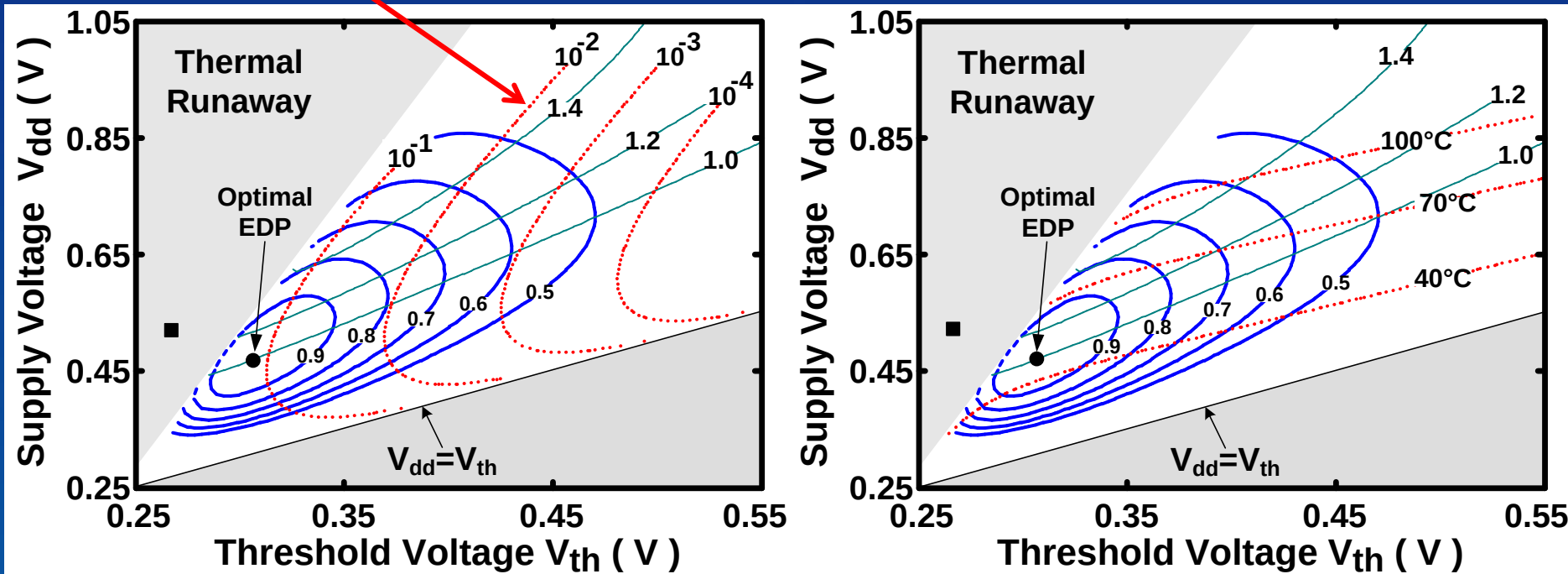
$$Energy = (P_{dynamic} + P_{static}) \cdot T_g L_d$$



EDP contours: 0.5 implies $EDP = 2 EDP_{opt}$

Electrothermally-Coupled EDP

Iso-leakage curves: leakage-power/total-power



Lin et al., TVLSI 2008

- ❖ A shift in optimal point, EDP and performance contours
- ❖ An overall change in shape of EDP contours
- ❖ Iso-temperature curves generated using self-consistent methodology—provide additional thermal (or reliability) constraint
- ❖ Operation region restricted by electrothermal constraints

Generalized Metric for Optimization

❖ EDP is not the only metric

❖ Other Metrics.....

EDP is Energy X Delay = PT^2

PDP is Power X Delay = PT

PEP is Power X Energy = P^2T



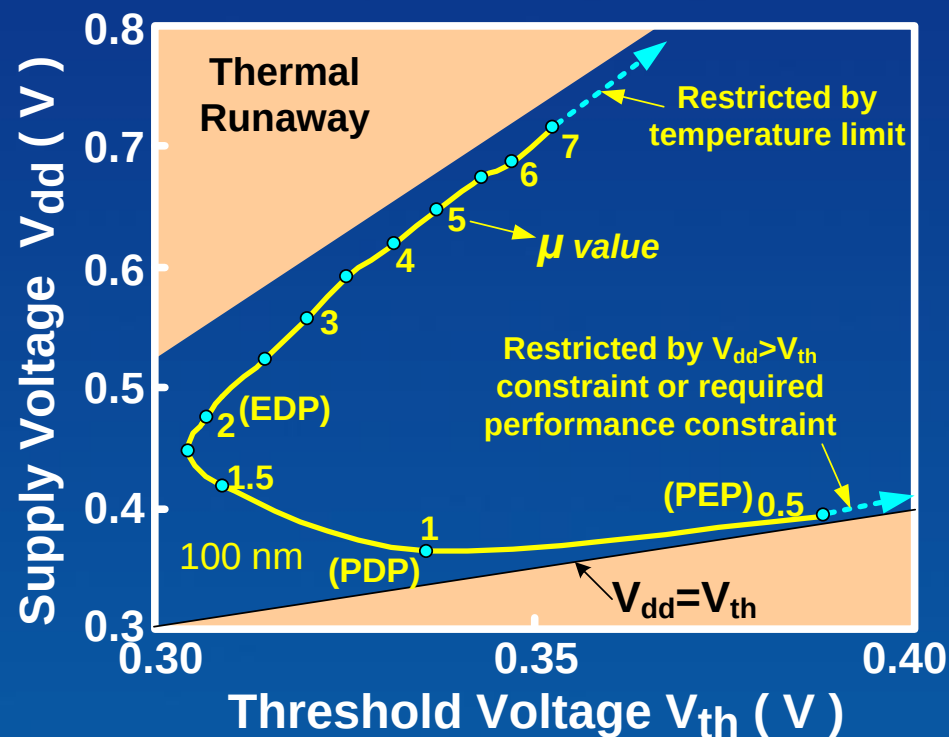
Generalized Metric: PT^μ

μ is the ratio of the exponent of delay over that of power ($\mu = 2$ for EDP)

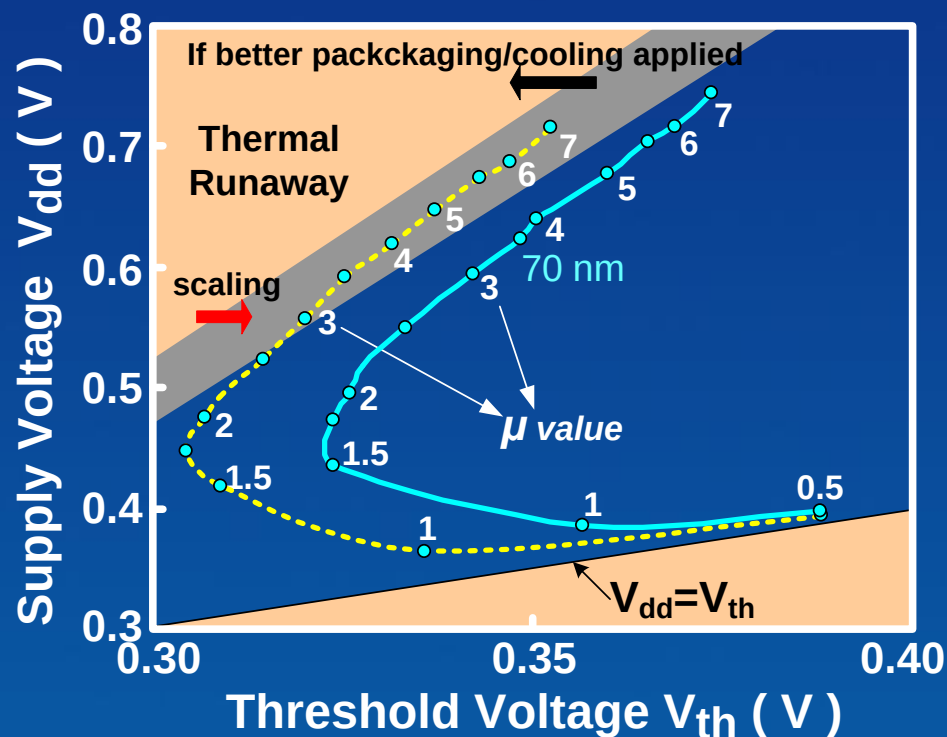
How to choose a design-specific metric ?

Optimal Operation Locus

Optimal operation locus for 100 nm node

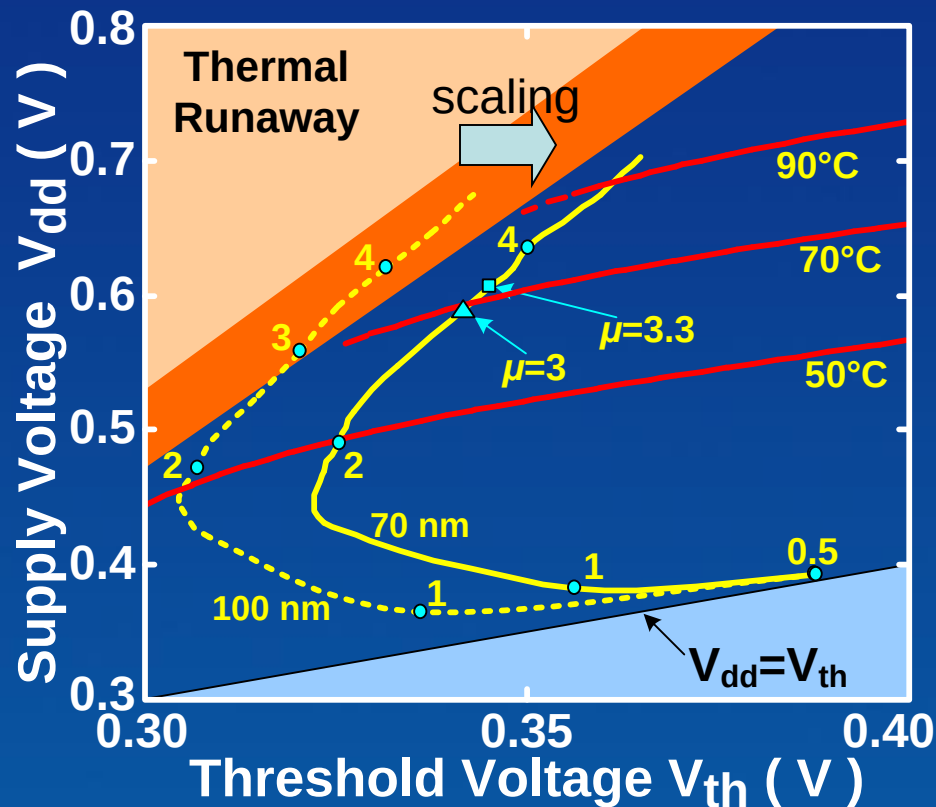
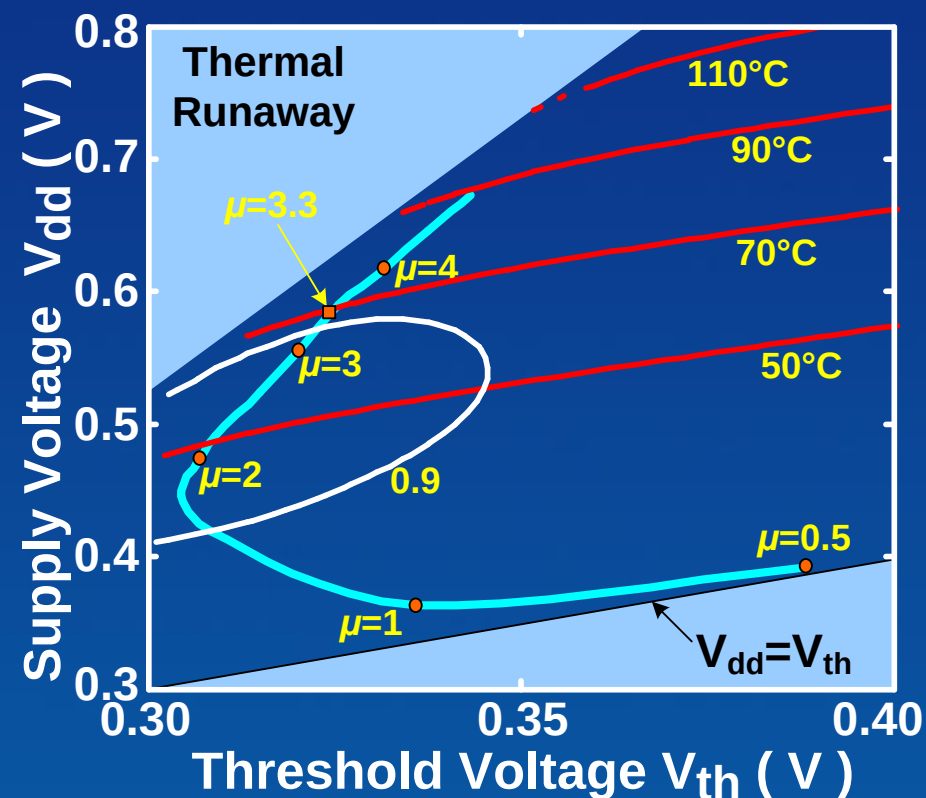


Effect of scaling on optimal operation locus



μ is determined by thermal and performance requirements

Thermal/Packaging Aware Design Optimization



- ❖ Choose an optimization metric to meet thermal/packaging requirements (For $T = 70^\circ\text{C}$, $\mu = 3.3$)
- ❖ Impact of scaling should be taken into account (For $T = 70^\circ\text{C}$, $\mu = 3$)

IC Cooling for Power/Thermal Management?

S-C. Lin and K. Banerjee, "Cool Chips: Opportunities and Implications for Power and Thermal Management," TED Vol. 55, No. 1, pp. 245-255, Jan 2008.

Efforts on Low-Power.....without hurting performance ...

❖ Device Engineering

- ❖ Enhanced Channel Mobility – Strained Silicon
- ❖ Reduced Gate Leakage – High-K Gate
- ❖ Reduced Junction Leakage – Nitrogen Doped

❖ Circuit Level

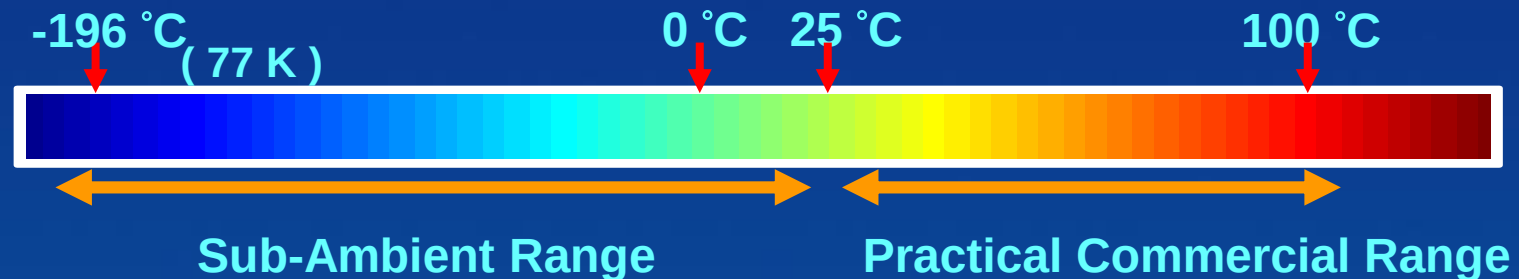
- ❖ Adaptive body-biasing, Dual V_{DD} -CMOS, Dual- V_{th}
- ❖ Sleep Transistor, Clock/Power Gating

❖ Micro-Architecture Level

- ❖ Multi-Core

Does IC Cooling Make Sense?

❖ Range of IC Cooling



❖ Prior Research on Cooling

❖ Analysis under Cryogenic Condition

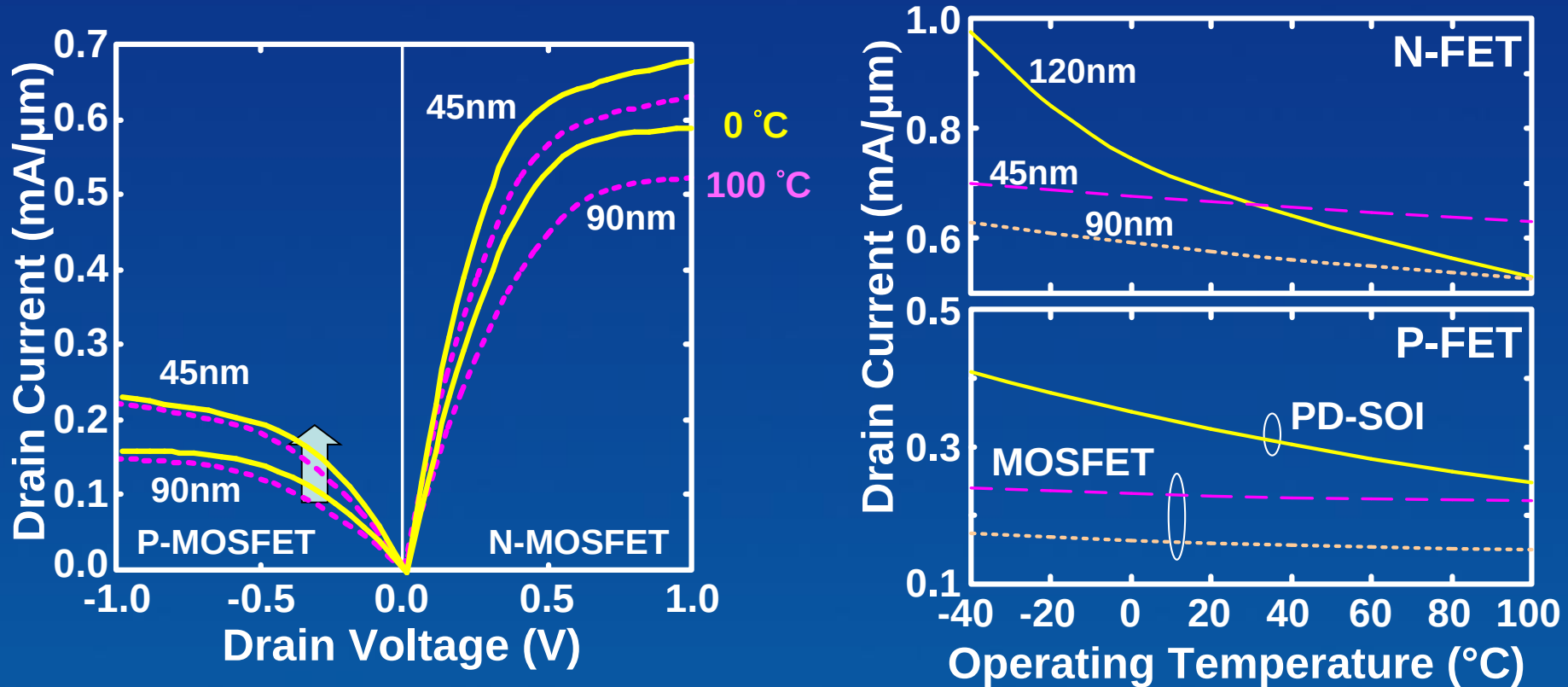
- Operating near liquid nitrogen temperature (77 K) requires complex cooling facilities
- NOT for commercial purpose

❖ Analysis of Performance under Cooling

- Does NOT consider electrothermal couplings
- Does NOT consider the system level power dissipation

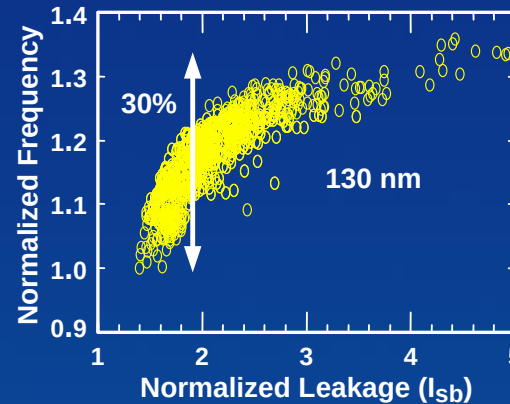
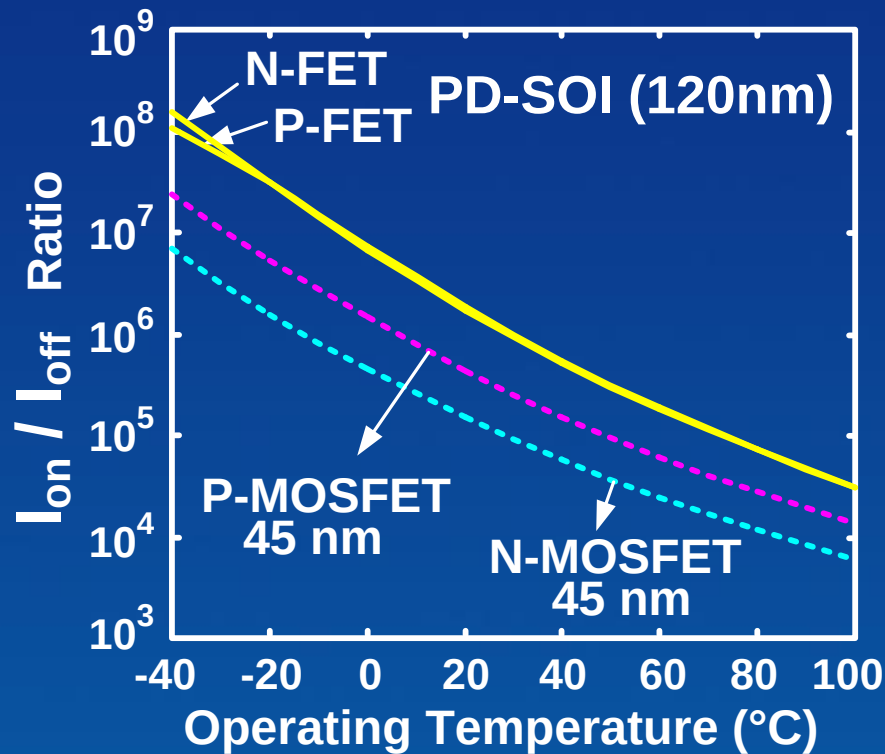
Cooling---Benefit at the Device Level

Transistor Drive Current Increases



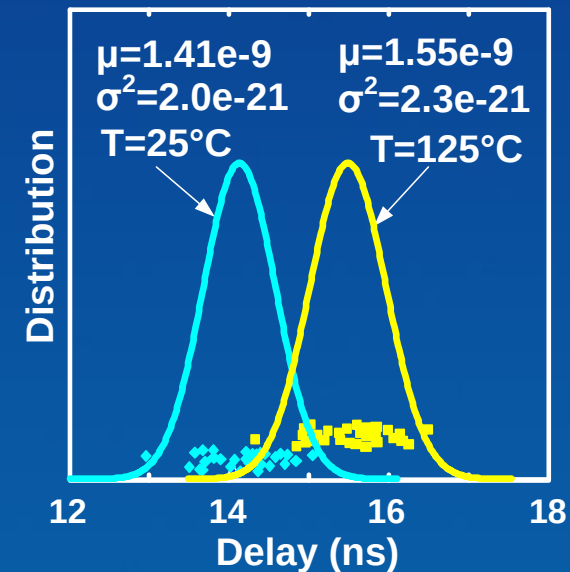
Higher drive current can be achieved by cooled operation across all technology nodes due to higher carrier mobility

Cooling---Benefit at the Circuit Level



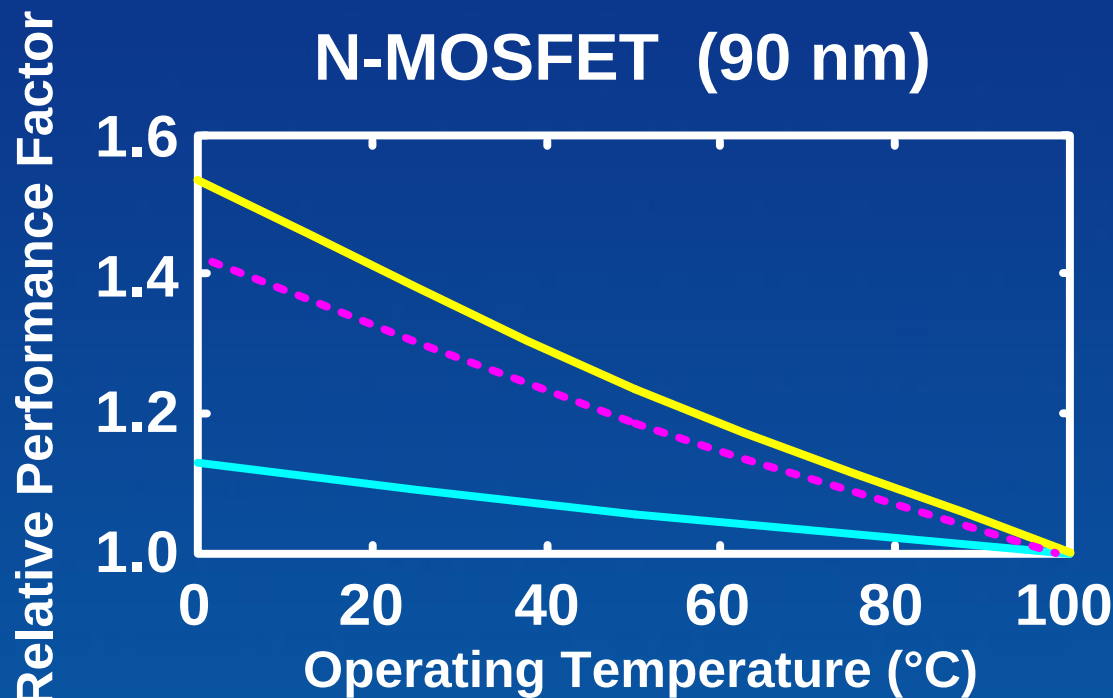
S. Borkar, Intel

9-stage Inverter Chain

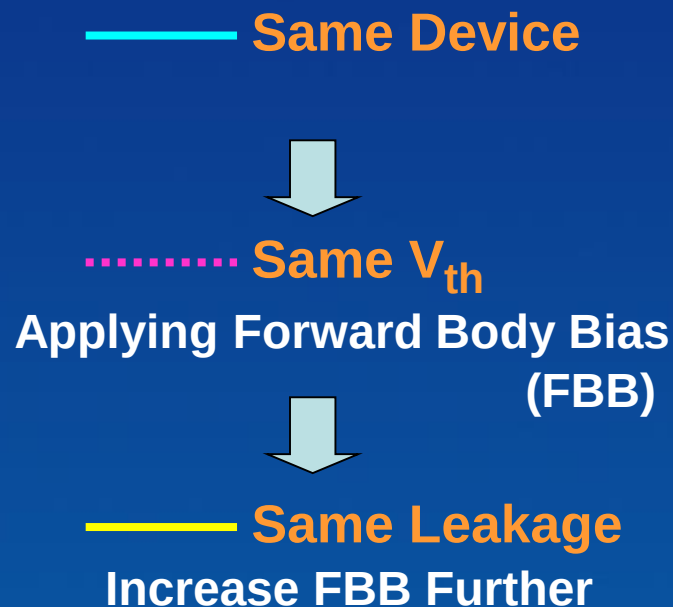


- ❖ Enhance I_{on} to I_{off} ratio
- ❖ Reduce propagation delay and variance
- ❖ Benefit back-end performance and reliability

Further Exploiting the Benefit of Cooling



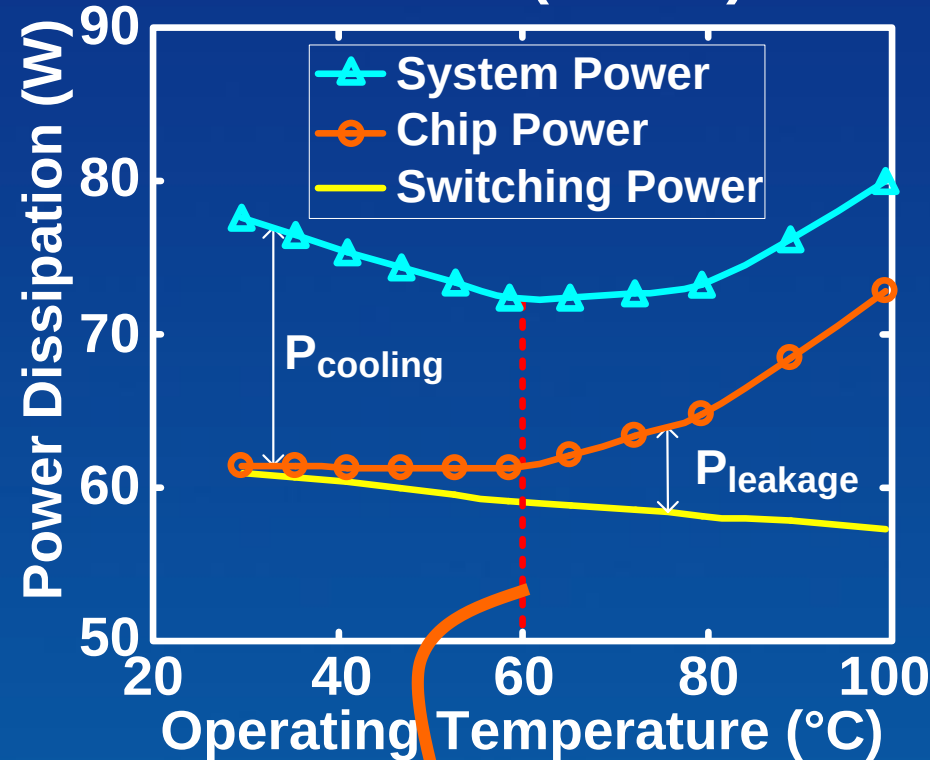
I. Aller et al., ISSCC 2000



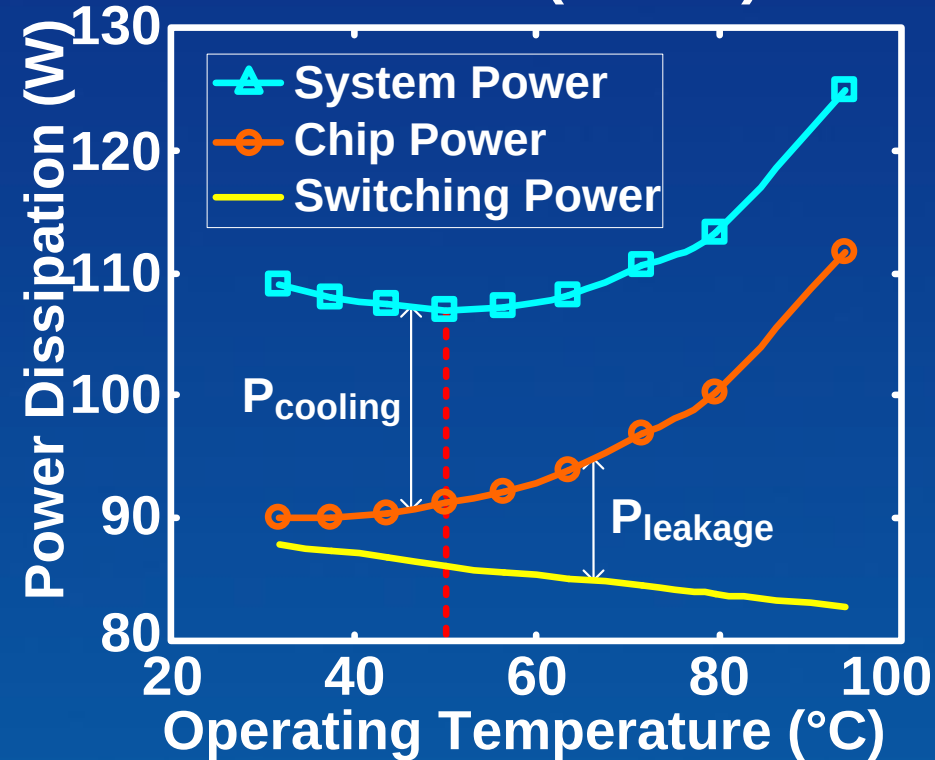
Performance can be further improved by different design strategies

Cooling---System Level Considerations

Module (90 nm)



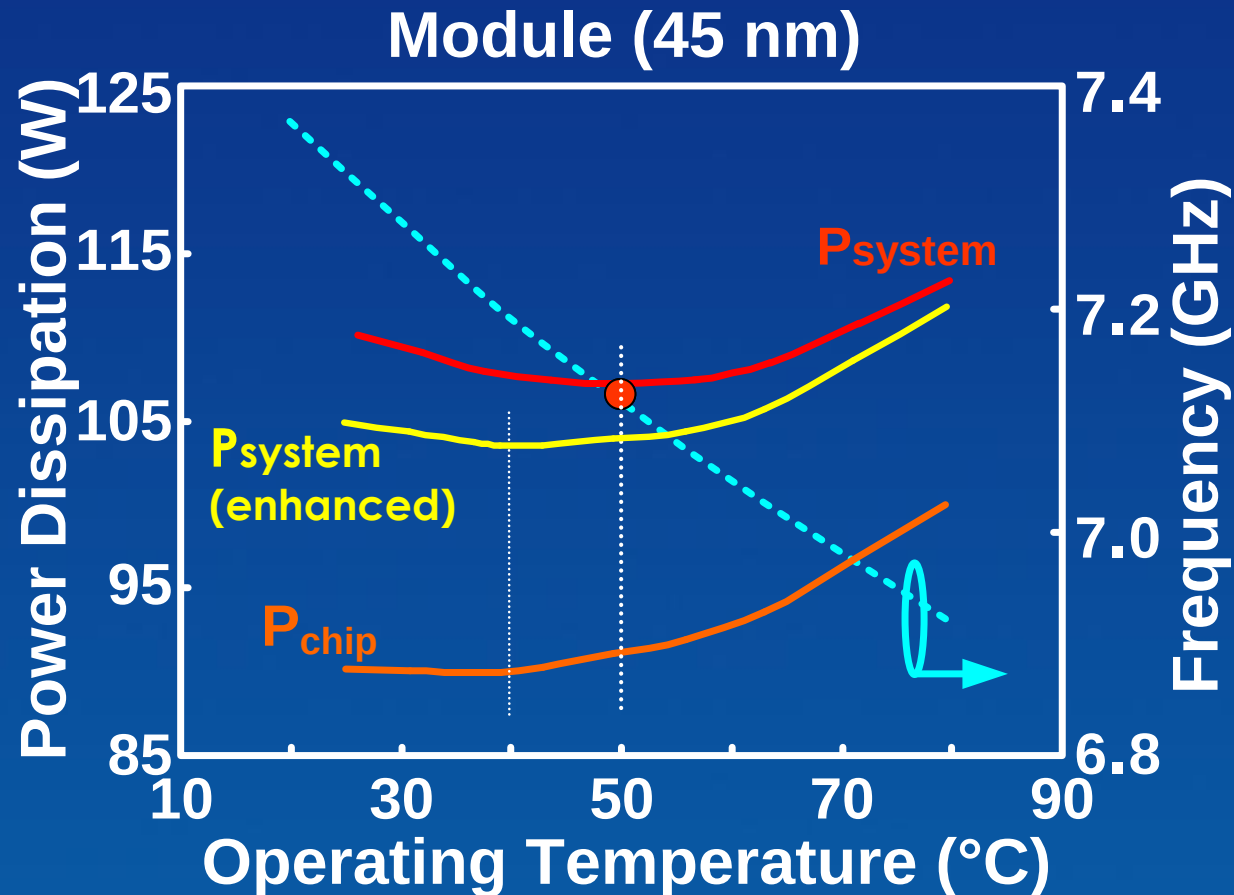
Module (45 nm)



Beyond this point, further cooling does not lead to any power saving.

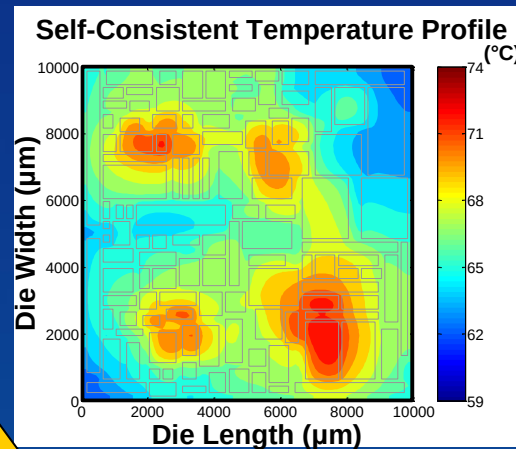
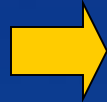
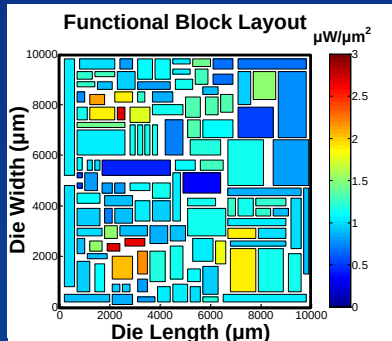
The limit occurs at a lower temperature as technology scales.

Extending the Practical Limit of Cooling

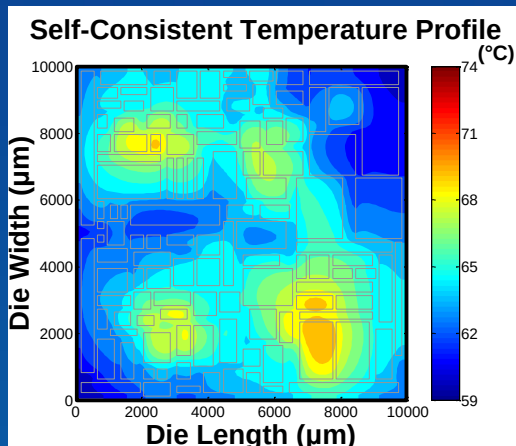


Practical limit can be further extended towards a lower temperature and higher performance is achieved by enhancing cooling efficiency

Hot-Spot Management

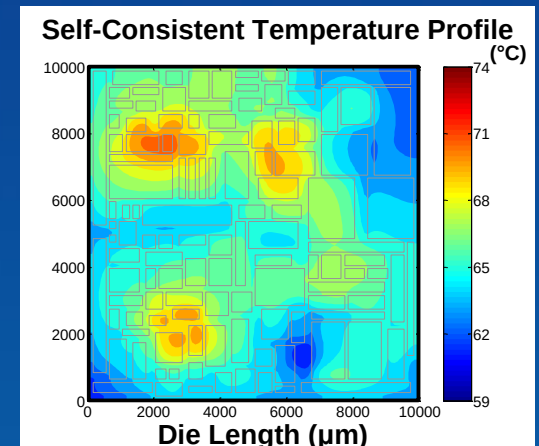


T_{MAX} decreases
but hot-spots remain



Global Cooling

Thermal resistance reduces 20%



Localized Cooling

Localized cooling will be more effective for hot-spot management

Conclusion

- ❖ For power/thermal management of nanoscale CMOS ICs, **electrothermal couplings** must be incorporated for trading-off chip-level power, performance, reliability, and cooling cost.
- ❖ An accurate leakage-aware **self-consistent power and silicon-substrate temperature-profile-estimation** technique has been developed for nanoscale CMOS technologies.
- ❖ A systematic methodology for power-performance optimization has been developed to **bring design and packaging closer**.
- ❖ **Chip cooling** combining device, circuit, and system level considerations can extend CMOS scaling.

Additional Issues....

- ❖ Extend CMOS scaling
 - ❖ Time per node can be expanded via cooling
- ❖ Application Based
 - ❖ High-performance servers
 - ❖ Hand-held applications
- ❖ Implications for Ultra Low-Voltage Applications
 - ❖ Positive Temperature Dependence